

IN THE CLAIMS:

Please cancel claims 1-17 without prejudice or disclaimer.

Claim 18 (original): A wafer alignment system comprising:

a photo-detector;

a wafer configured to be scanned by a beam from said photo-detector; wherein said wafer comprises an alignment target further comprising:

a reflective member; and

a non-reflective field configured to be proximate to said reflective member and comprising at least one of an absorptive material and a scattering structure, wherein said non-reflective field is configured to enhance contrast in the amount of said beam reflected to said photo-detector by said non-reflective field and said reflective member and thereby enhance wafer alignment.

Claim 19 (original): The wafer alignment system of claim 18, said non-reflective field comprising both said absorptive material and said scattering structure.

Claim 20 (original): The wafer alignment system of claim 18 wherein said absorptive material comprises a poly-crystalline material.

Claim 21 (original): The wafer alignment system of claim 18 wherein said scattering structure comprises at least one edge slope.

Claim 22 (original): The wafer alignment system of claim 21 wherein said at least one edge slope is formed by boundaries between areas of poly and no poly.

Claim 23 (original): The wafer alignment system of claim 22 wherein said edge slopes are created in a checkerboard pattern.

Claim 24 (original): The wafer alignment system of claim 23 wherein said member comprises a metal.

Claim 25 (original): A method of aligning a wafer comprising the steps of:

shining a beam of light from a light source onto a wafer;

reflecting a portion of said beam of light from a reflective member to a photo-detector;

reflecting a reduced portion of said beam of light from a non-reflective field to said photo-detector, wherein said reflecting a reduced portion step comprises at least one of the steps of: absorbing a portion of said beam of light and reflecting a portion of said beam of light away from said photo-detector;

identifying a current position of said wafer based on the contrast in said beam of light reflected from said reflective member and said non-reflective field; and

adjusting the position of said wafer based on said current position of said wafer.

Claim 26 (original): The method of claim 25, wherein said reflecting a reduced portion step comprises the steps of: absorbing a portion of said beam of light and reflecting a portion of said beam of light away from said photo-detector.

Claim 27 (original): The method of claim 25 wherein said absorbing step is facilitated by a poly-crystalline material.

Claim 28 (original): The method of claim 25 wherein said step of reflecting a portion of said beam of light away from said photo-detector includes scattering said beam of light with at least one edge slope.

Claim 29 (original): The method of claim 28 wherein said at least one edge slope is formed by boundaries between areas of poly and no poly.

Claim 30 (original): The method of claim 29 wherein said absorbing and said scattering are caused by edge slopes created in a checkerboard pattern with said poly and no poly areas.